

## General Description

The GreenMOS<sup>®</sup> high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS<sup>®</sup> Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

## Features

- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity




## Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

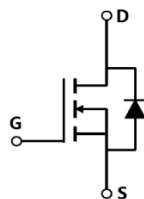
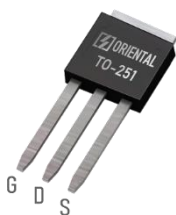
## Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	700	V
$I_{D, pulse}$	21	A
$R_{DS(ON), max} @ V_{GS}=10V$	760	m $\Omega$
$Q_g$	7.4	nC

## Marking Information

Product Name	Package	Marking
OSG65R760AF	TO251	OSG65R760A

## Package & Pin Information



**Absolute Maximum Ratings** at  $T_j=25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	650	V
Gate-source voltage	$V_{GS}$	$\pm 30$	V
Continuous drain current <sup>1)</sup> , $T_C=25^\circ\text{C}$	$I_D$	7	A
Continuous drain current <sup>1)</sup> , $T_C=100^\circ\text{C}$		4.4	
Pulsed drain current <sup>2)</sup> , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	21	A
Continuous diode forward current <sup>1)</sup> , $T_C=25^\circ\text{C}$	$I_S$	7	A
Diode pulsed current <sup>2)</sup> , $T_C=25^\circ\text{C}$	$I_{S, pulse}$	21	A
Power dissipation <sup>3)</sup> , $T_C=25^\circ\text{C}$	$P_D$	37	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	130	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$ , $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	3.4	$^\circ\text{C/W}$
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62	$^\circ\text{C/W}$

**Electrical Characteristics** at  $T_j=25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	650			V	$V_{GS}=0\text{ V}$ , $I_D=250\ \mu\text{A}$
		700	750			$V_{GS}=0\text{ V}$ , $I_D=250\ \mu\text{A}$ , $T_j=150^\circ\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}$ , $I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.66	0.76	$\Omega$	$V_{GS}=10\text{ V}$ , $I_D=3.5\text{ A}$
			1.6			$V_{GS}=10\text{ V}$ , $I_D=3.5\text{ A}$ , $T_j=150^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=650\text{ V}$ , $V_{GS}=0\text{ V}$

### Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		354.2		pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$		31.4		pF	
Reverse transfer capacitance	$C_{rss}$		1.54		pF	
Turn-on delay time	$t_{d(on)}$		17.6		ns	$V_{GS}=10\text{ V}$ , $V_{DS}=400\text{ V}$ , $R_G=25\ \Omega$ , $I_D=5\text{ A}$
Rise time	$t_r$		11.4		ns	
Turn-off delay time	$t_{d(off)}$		27.2		ns	
Fall time	$t_f$		24.4		ns	

### Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		7.4		nC	$V_{GS}=10\text{ V}$ , $V_{DS}=400\text{ V}$ , $I_D=5\text{ A}$
Gate-source charge	$Q_{gs}$		1.9		nC	
Gate-drain charge	$Q_{gd}$		3.3		nC	
Gate plateau voltage	$V_{plateau}$		5.9		V	

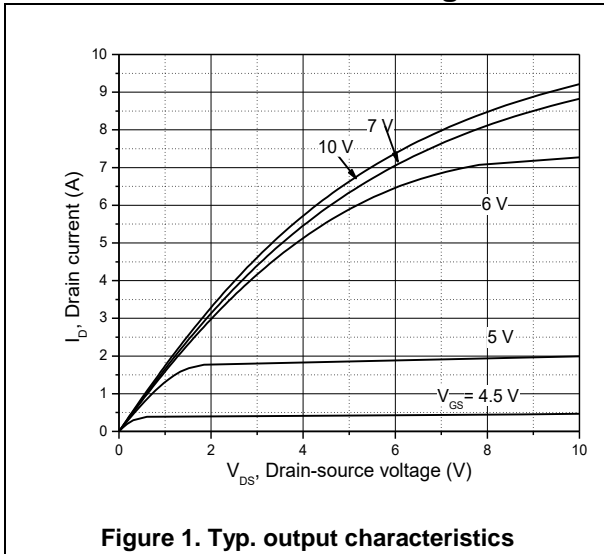
### Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=7\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		146		ns	$V_R=400\text{ V}$ , $I_S=5\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		0.98		$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$		11.6		A	

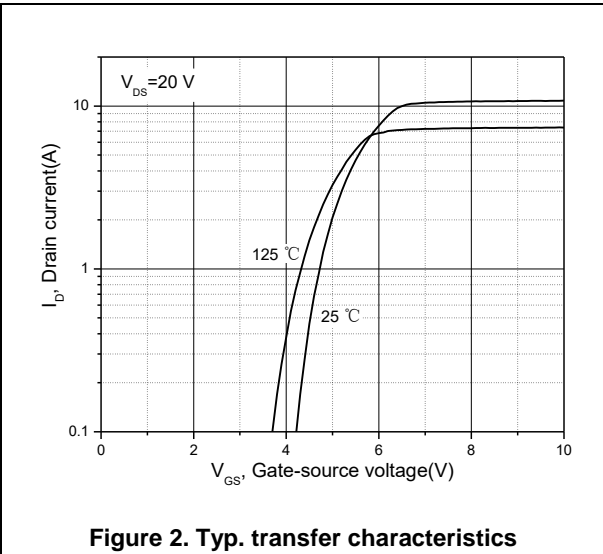
### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=50\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=20\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

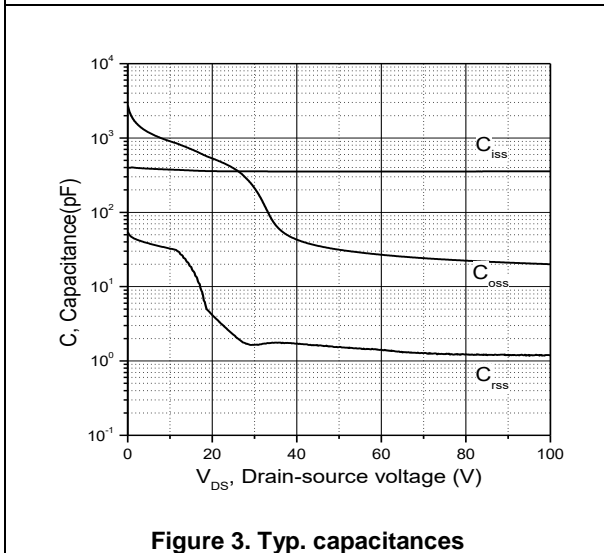
**Electrical Characteristics Diagrams**



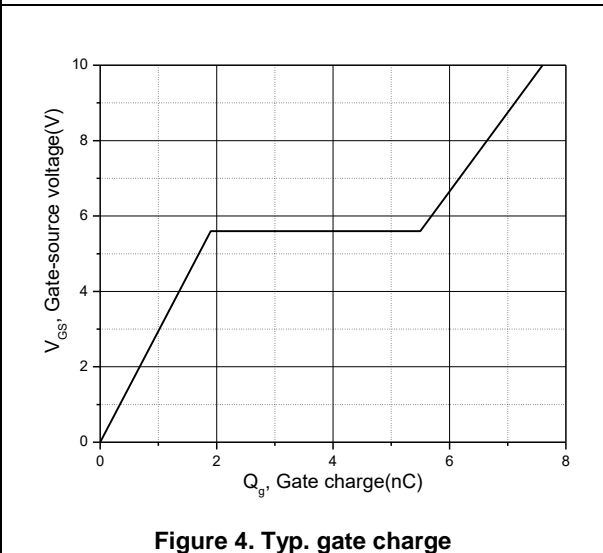
**Figure 1. Typ. output characteristics**



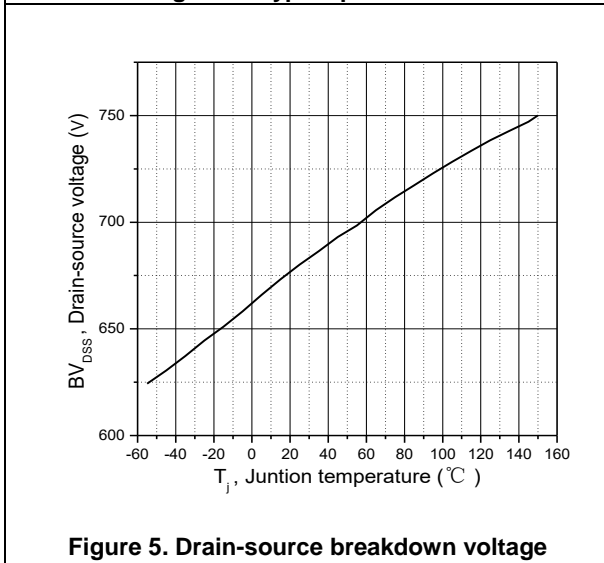
**Figure 2. Typ. transfer characteristics**



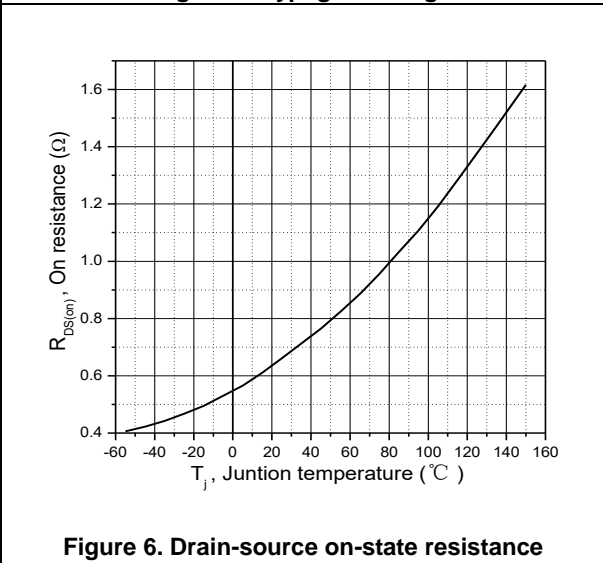
**Figure 3. Typ. capacitances**



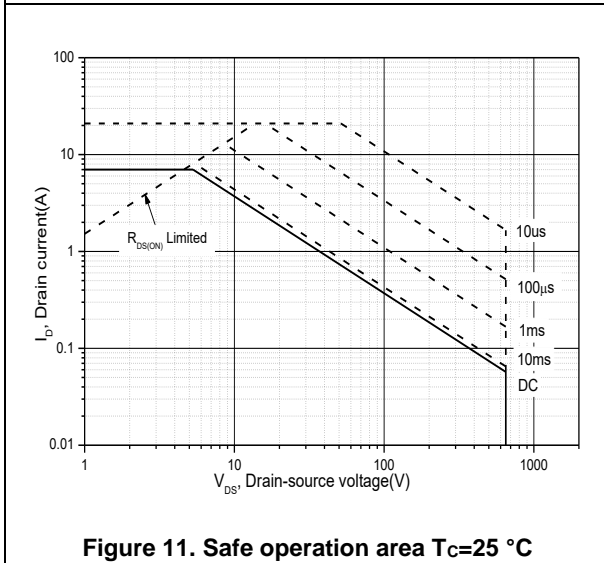
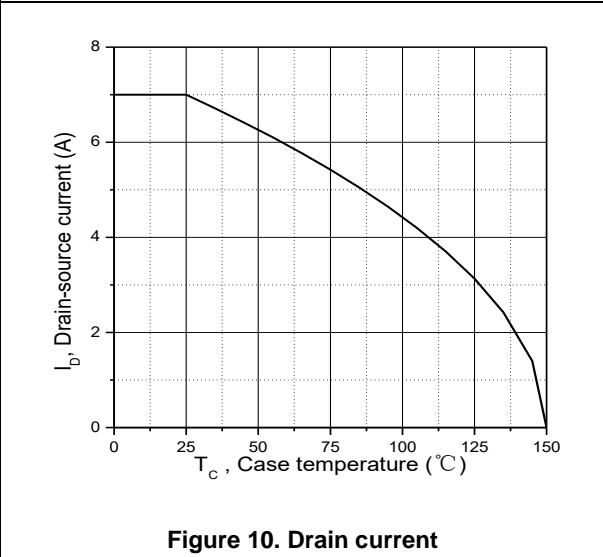
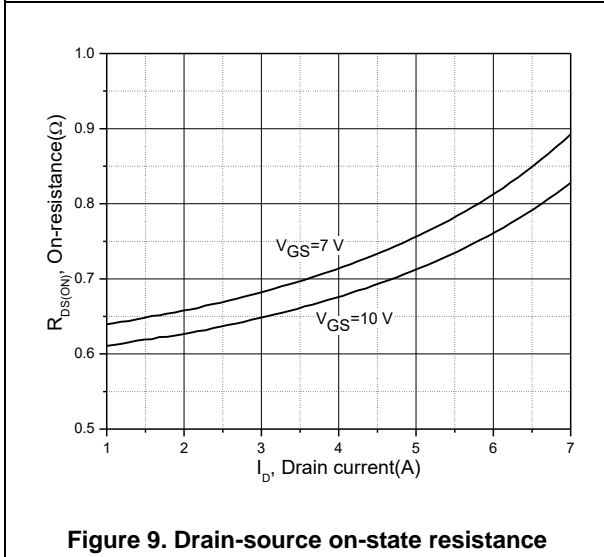
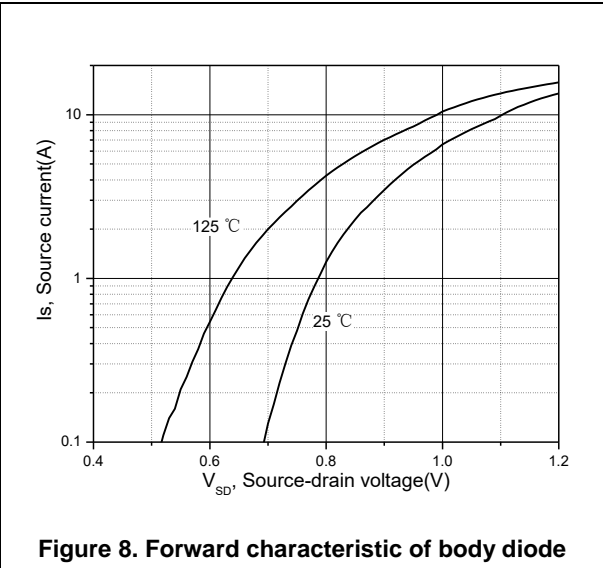
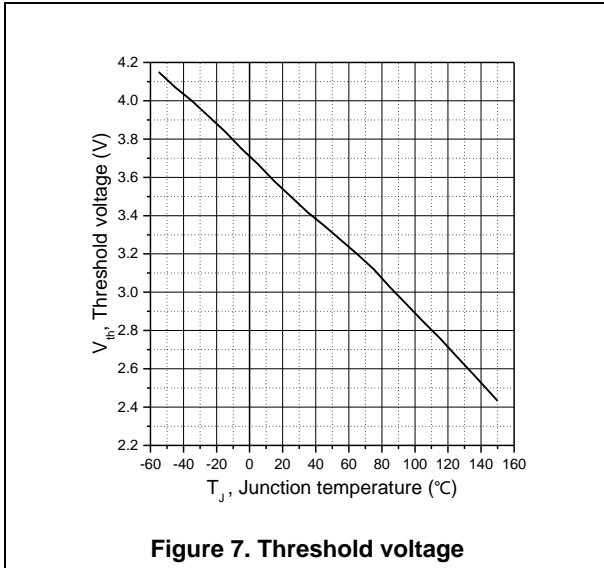
**Figure 4. Typ. gate charge**



**Figure 5. Drain-source breakdown voltage**



**Figure 6. Drain-source on-state resistance**



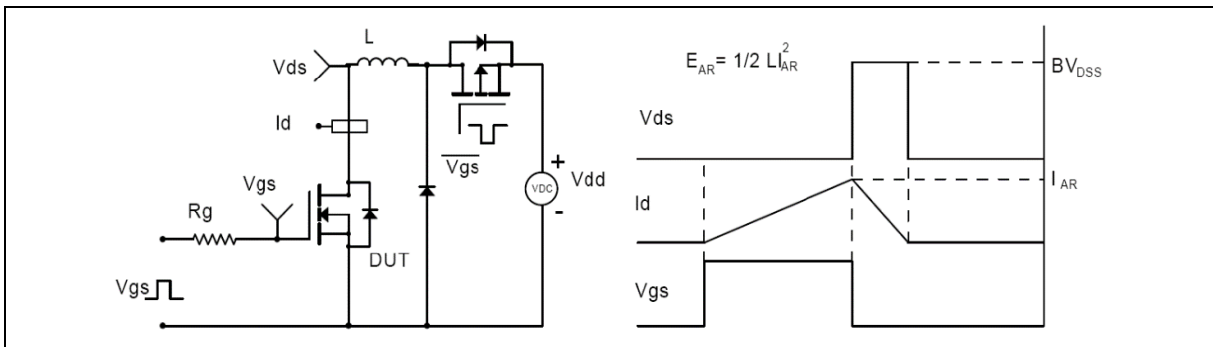
**Test circuits and waveforms**



**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**

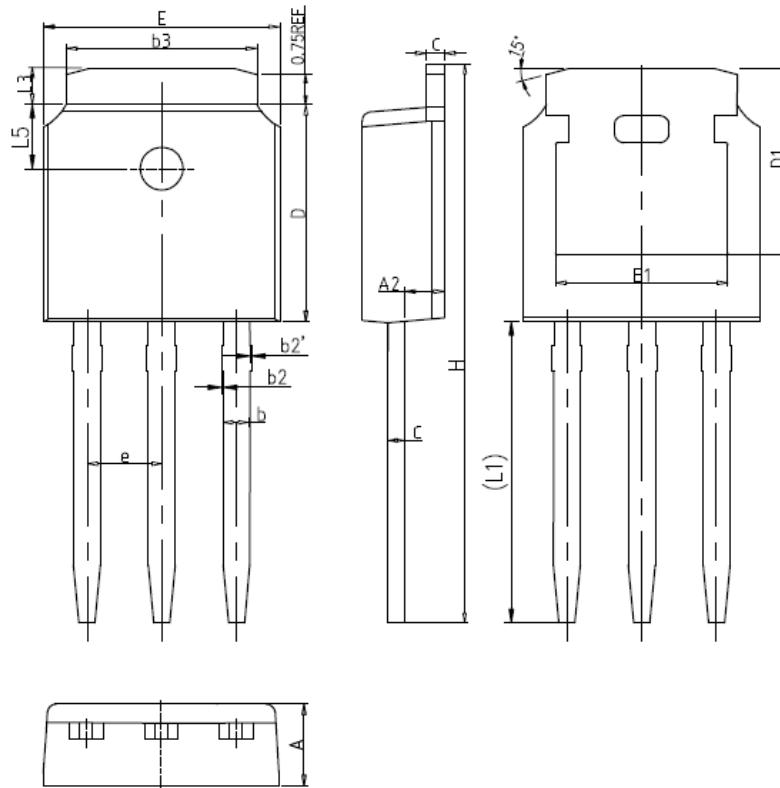


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

**Package Information**



Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

Version 1: TO251-C package outline dimension

## Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO251-C	75	66	4950	6	29700

## Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R760AF	TO251	yes	yes	yes

## Legal Disclaimer

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